

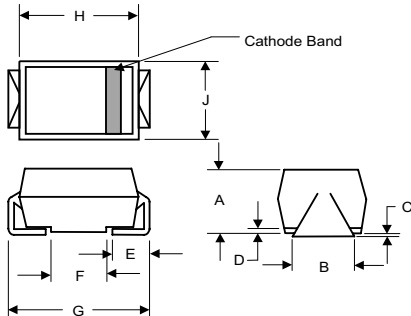


# FR1A THRU FR1M

## SURFACE MOUNT FAST RECOVERY RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere

### DO-214AA (HSMB) (Round Lead)



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.078	.116	1.98	2.95	
B	.075	.089	1.90	2.25	
C	.002	.008	.05	.20	
D	—	.02	—	.51	
E	.035	.055	.90	1.40	
F	.065	.091	1.65	2.32	
G	.205	.224	5.21	5.69	
H	.160	.180	4.06	4.57	
J	.130	.155	3.30	3.94	

### FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Low reverse leakage
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed:  
250°C/10 seconds at terminals
- ◆ Glass passivated chip junction

### MECHANICAL DATA

**Case** : JEDEC DO-214AA molded plastic body over passivated chip

**Terminals** : Solder plated, solderable per MIL-STD-750, Method 2026

**Polarity** : Color band denotes cathode end

**Mounting Position** : Any

**Weight** : 0.005 ounce, 0.138 grams

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

MDD Catalog Number	SYMBOLS	FR1A	FR1B	FR1D	FR1G	FR1J	FR1K	FR1M	UNITS
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at $T_L=90^\circ\text{C}$	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	50.0							Amps
Maximum instantaneous forward voltage at 1.0A	$V_F$	1.3							Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=125^\circ\text{C}$	$I_R$	5.0 200.0							$\mu\text{A}$
Maximum reverse recovery time (NOTE 1)	$t_{rr}$	150				250	500		ns
Typical junction capacitance (NOTE 2)	$C_J$	40.0							pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	15.0							$^\circ\text{C}/\text{W}$
Operating junction and storage temperature range	$T_J, T_{STG}$	-50 to +150							$^\circ\text{C}$

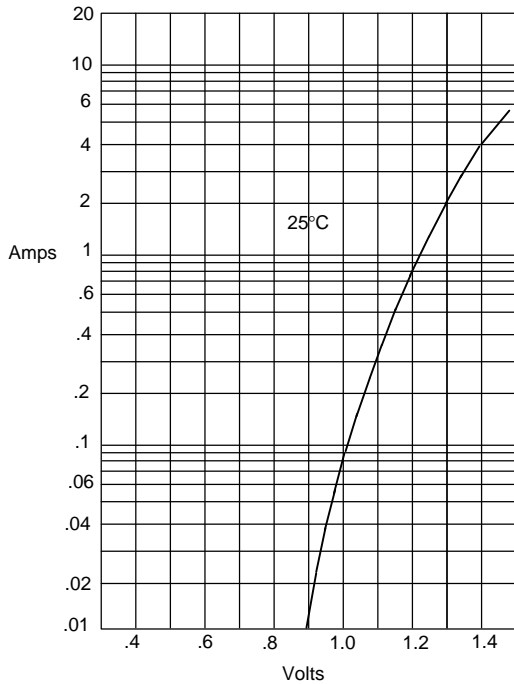
**Note:** 1. Reverse recovery condition  $I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$   
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.  
3. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

MDD ELECTRONIC

# RATINGS AND CHARACTERISTIC CURVES FR1A THRU FR1M

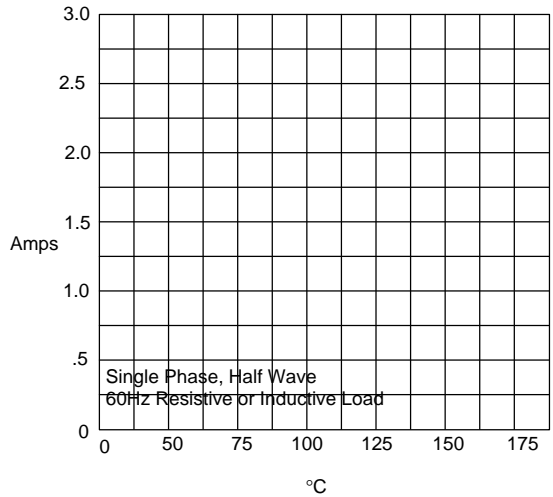
Figure 1

Typical Forward Characteristics



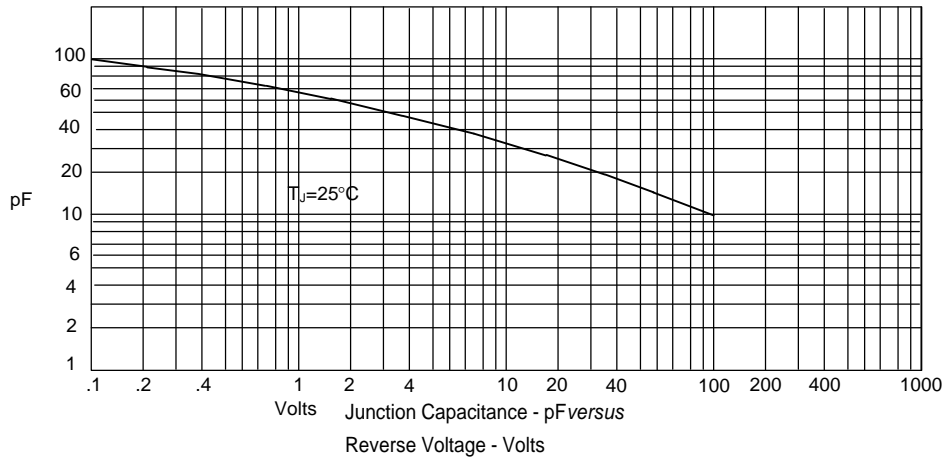
Instantaneous Forward Current - Amperes *versus*  
Instantaneous Forward Voltage - Volts

Figure 2  
Forward Derating Curve



Average Forward Rectified Current - Amperes *versus*  
Ambient Temperature - °C

Figure 3  
Junction Capacitance



# RATINGS AND CHARACTERISTIC CURVES FR1A THRU FR1M

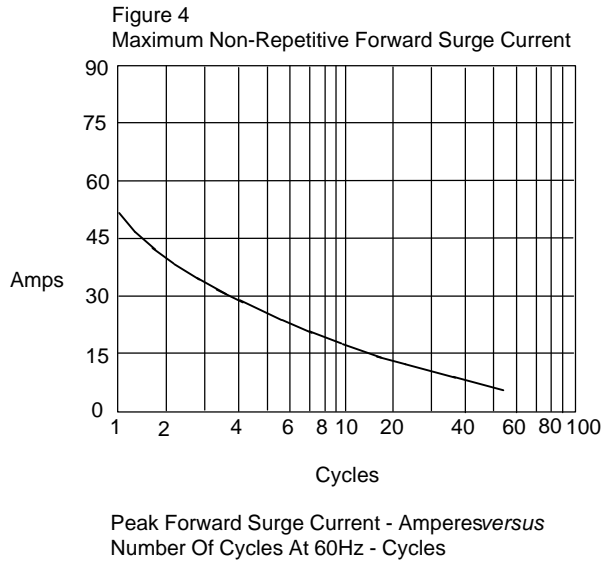
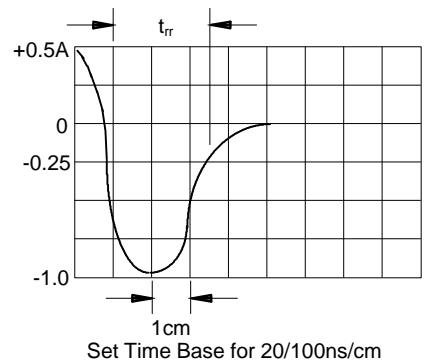
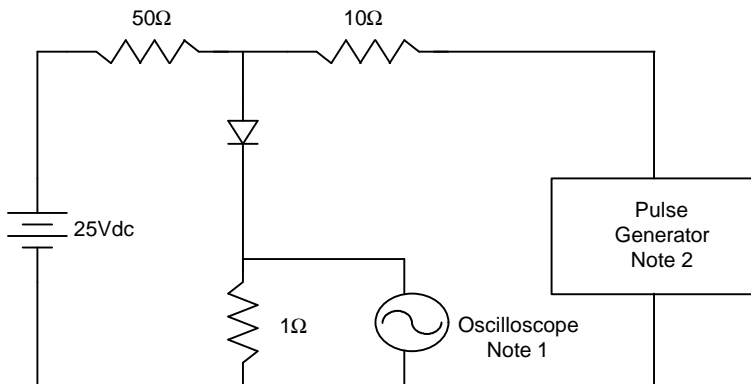


Figure 5  
Reverse Recovery Time Characteristic And Test Circuit Diagram



Notes:

1. Rise Time = 7ns max.  
Input impedance = 1 megohm, 22pF
2. Rise Time = 10ns max.  
Source impedance = 50 ohms
3. Resistors are non-inductive